

MITSUBISHI Nch POWER MOSFET

FS7VS-14A

HIGH-SPEED SWITCHING USE

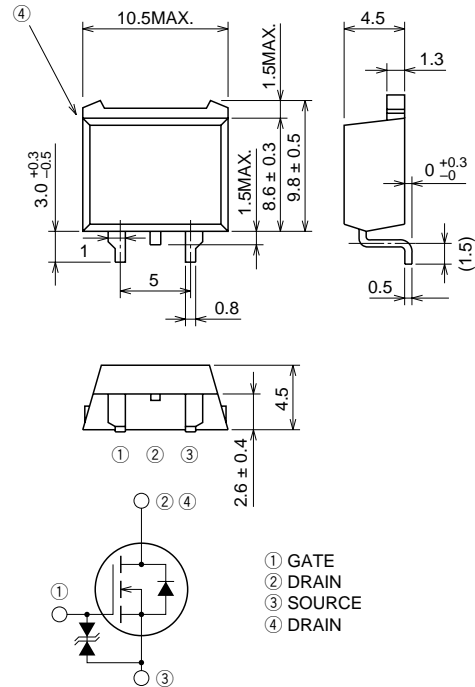
FS7VS-14A



- V_{DSS} 700V
- r_{DS (ON)} (MAX) 1.82Ω
- I_D 7A

OUTLINE DRAWING

Dimensions in mm



TO-220S

APPLICATION

SMPS, DC-DC Converter, battery charger, power supply of printer, copier, HDD, FDD, TV, VCR, personal computer etc.

MAXIMUM RATINGS (T_c = 25°C)

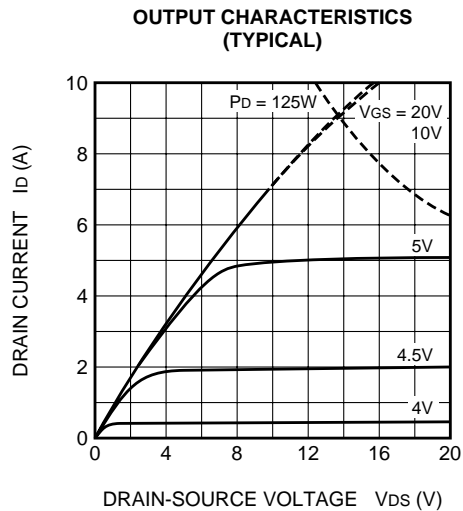
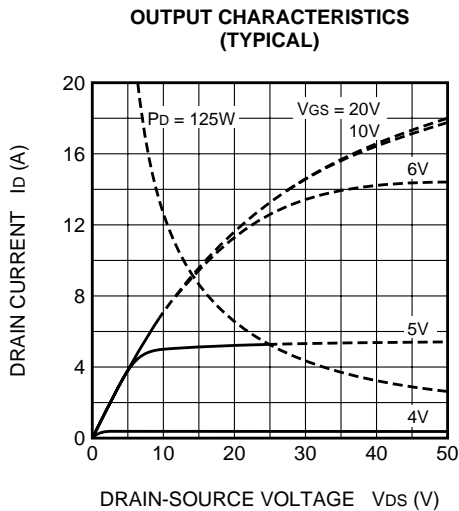
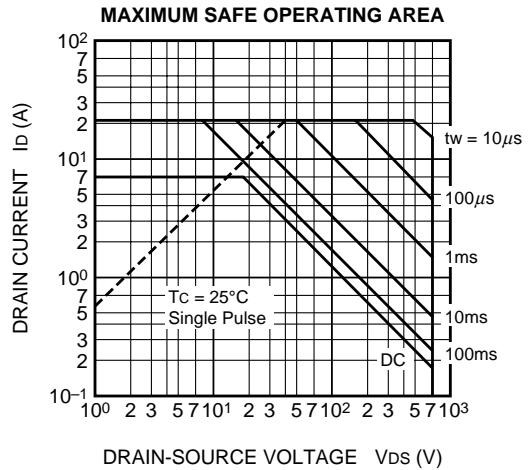
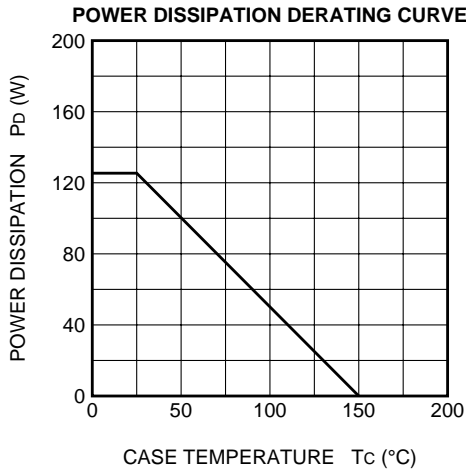
Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	700	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±30	V
I _D	Drain current		7	A
I _{DM}	Drain current (Pulsed)		21	A
P _D	Maximum power dissipation		125	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	1.2	g

Feb.1999

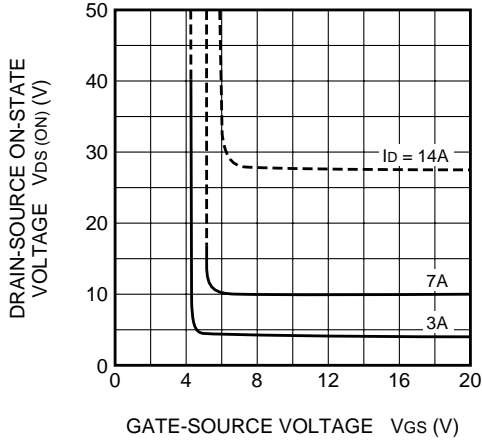
ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, Vgs = 0V	700	—	—	V
V (BR) GSS	Gate-source breakdown voltage	Igs = ±100μA, Vds = 0V	±30	—	—	V
IgSS	Gate-source leakage current	Vgs = ±25V, Vds = 0V	—	—	±10	μA
IdSS	Drain-source leakage current	Vds = 700V, Vgs = 0V	—	—	1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, Vds = 10V	2	3	4	V
rDS (ON)	Drain-source on-state resistance	Id = 3A, Vgs = 10V	—	1.40	1.82	Ω
VDS (ON)	Drain-source on-state voltage	Id = 3A, Vgs = 10V	—	4.20	5.46	V
yfs	Forward transfer admittance	Id = 3A, Vds = 10V	3.6	6.0	—	S
Ciss	Input capacitance	Vds = 25V, Vgs = 0V, f = 1MHz	—	1050	—	pF
Coss	Output capacitance		—	100	—	pF
Crss	Reverse transfer capacitance		—	24	—	pF
td (on)	Turn-on delay time		—	20	—	ns
tr	Rise time	VDD = 200V, Id = 3A, Vgs = 10V, RGEN = RGS = 50Ω	—	22	—	ns
td (off)	Turn-off delay time		—	110	—	ns
tf	Fall time		—	35	—	ns
VSD	Source-drain voltage	Is = 3A, Vgs = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	1.0	°C/W

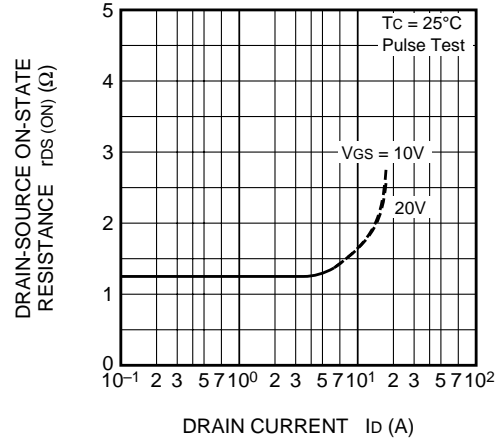
PERFORMANCE CURVES



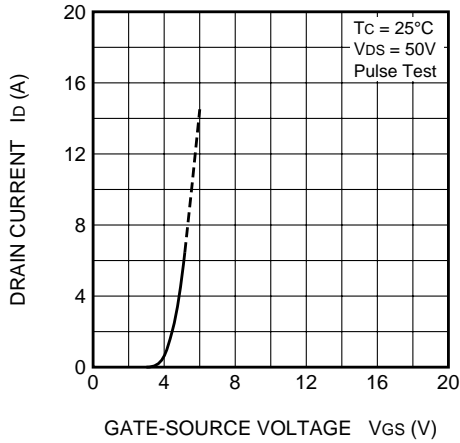
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



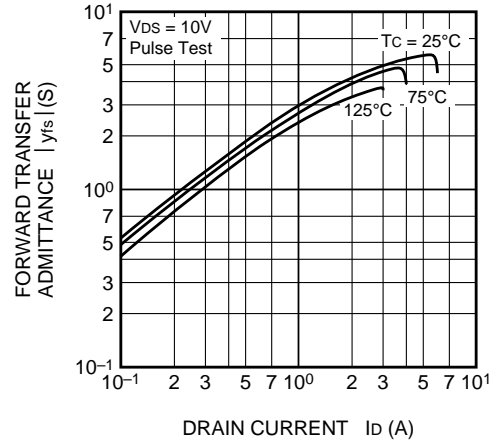
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



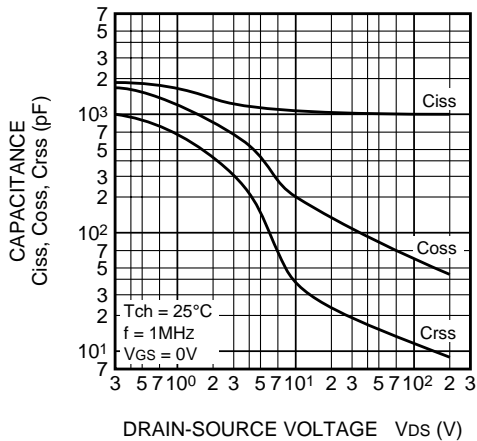
TRANSFER CHARACTERISTICS (TYPICAL)



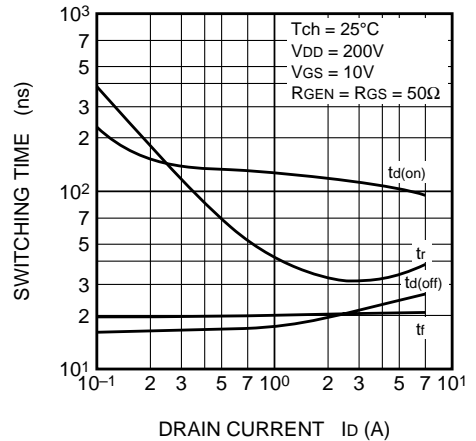
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



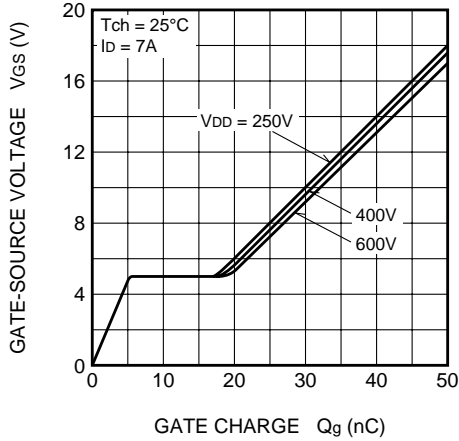
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



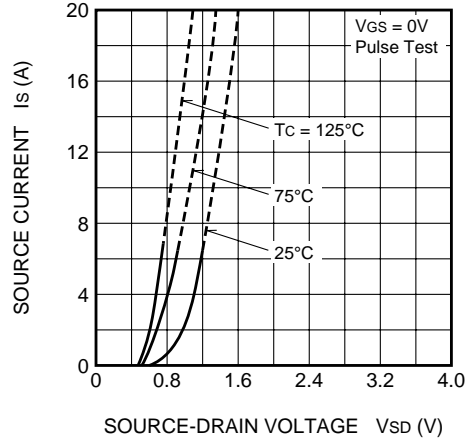
SWITCHING CHARACTERISTICS (TYPICAL)



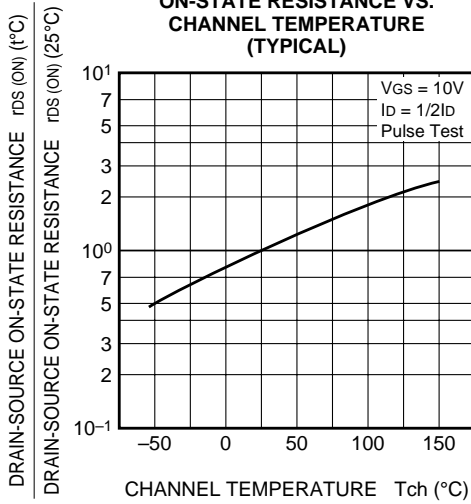
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



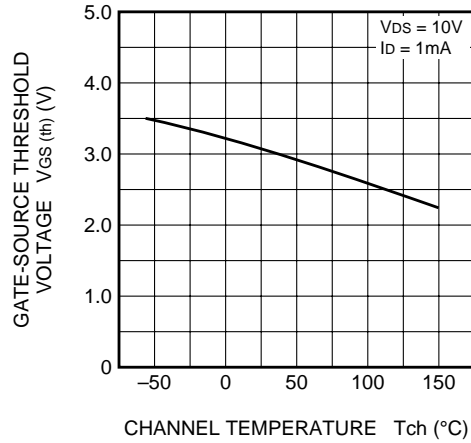
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



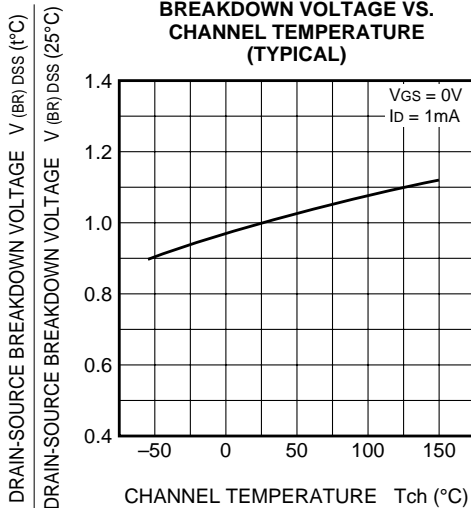
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

